TOSHIBA Transistor Silicon PNP Epitaxial Type

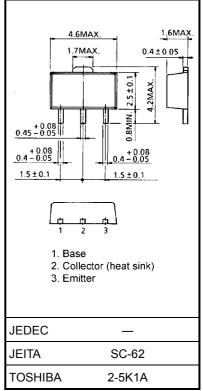
2SA2070

High-Speed Switching Applications DC-DC Converter Applications

- High DC current gain: $h_{FE} = 200$ to 500 (I_C = -0.1 A)
- Low collector-emitter saturation voltage: $V_{CE (sat)} = 0.20 V (max)$
- High-speed switching: $t_f = 70 \text{ ns}$ (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	-50	V	
Collector-emitter voltage		V _{CEO}	-50	V	
Emitter-base voltage		V _{EBO}	-7	V	
Collector current	DC	Ι _C	-1.0	А	
	Pulse	I _{CP} -2.0			
Base current		Ι _Β	-0.1	А	
Collector power dissipation	DC	De (Note)	1.0	W	
	t = 10 s	P _C (Note)	2.0	vv	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



Note: Mounted on FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm^2)

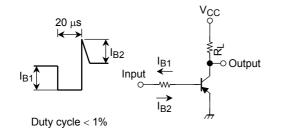
Weight: 0.05 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current		I _{CBO}	$V_{CB} = -50 \text{ V}, \text{ I}_{E} = 0$	_	_	-100	nA	
Emitter cut-off current		I _{EBO}	$V_{EB} = -7 V, I_C = 0$	—	_	-100	nA	
Collector-emitter breakdown voltage		V (BR) CEO	I _C = −10 mA, I _B = 0	-50	_	_	V	
DC current gain		h _{FE} (1)	$V_{CE} = -2 V, I_C = -0.1 A$	200	_	500		
		h _{FE} (2)	$V_{CE} = -2 V, I_C = -0.3 A$	125		-		
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = −0.3 A, I _B = −0.01 mA	_		-0.20	V	
Base-emitter saturation voltage		V _{BE (sat)}	I _C = −0.3 A, I _B = −0.01 mA	_		-1.10	V	
Collector output capacitance		C _{ob}	V _{CB} = −10 V, I _E = 0, f = 1 MHz	_	8	_	pF	
Switching time	Rise time	tr	See Figure 1 circuit diagram.	_	60	_	ns	
	Storage time	t _{stg}	V _{CC} ≈ –30 V, R _L = 100 Ω	_	280	_		
	Fall time	t _f	$I_{B1} = -I_{B2} = -10 \text{ mA}$	—	70	—		

Unit: mm

Marking



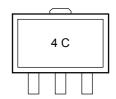
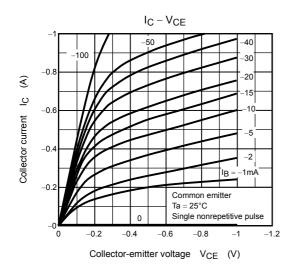
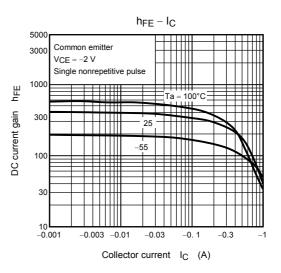
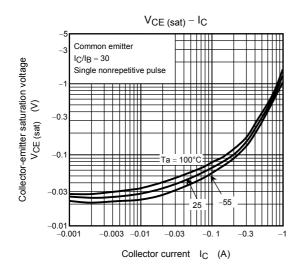


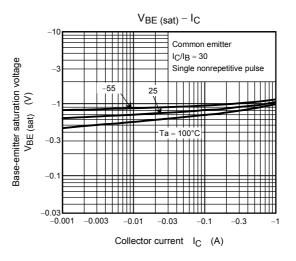
Figure 1 Switching Time Test Circuit & Timing Chart

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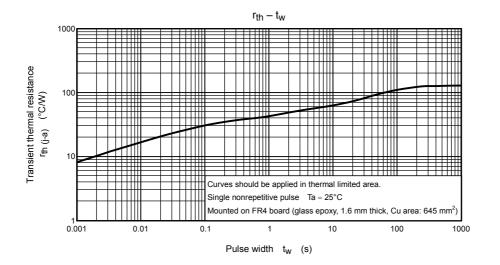








$I_{C} - V_{BE}$ Common emitter $V_{CE} = -2 V$ Single nonrepetitive pulse -0.8 E Collector current IC -0.6 -0.4 . 100° 25 -0.2 55 0 0 -0.2 -0.4 -0.6 -0.8 -1.0 -1.2 Base-emitter voltage VBE (V)



Safe Operating Area -10 ms* 1 ms* 100 μs* ₹ IC max (pulsed)* 10 ms* 10 μs <u>ں</u> max (continuous 10 Collector current DC operation (Ta = 25° C) 100 ms* -0.3 *: Single nonrepetitive pulse Ta = 25°C Note that the curves for 100 ms, 10 s and DC operation will be different when the devices aren't mounted on an FR4 board (glass epoxy, 1,6 mm thick, Cu area: 645 mm²). These characteristic curves must be derated linearly with increase in temperature. -0.1 CEO max Ħ -0.03 with increase in temperature. -0.01 -0.1 -0.3 -1 -3 -10 -30 -100 Collector-emitter voltage V_{CE} (V)

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